

ABSTRACT

The present invention refers to a method of forming a silicon dioxide layer by thermally oxidizing at least one monocrystalline silicon surface region on a semiconductor substrate. The silicon surface region has a curved surface. The method
5 can include providing a semiconductor substrate having at least one monocrystalline silicon surface region having a curved surface, roughening the surface of the at least one monocrystalline silicon surface region to produce a layer of porous silicon, and thermally oxidizing the at least one roughened monocrystalline silicon surface.